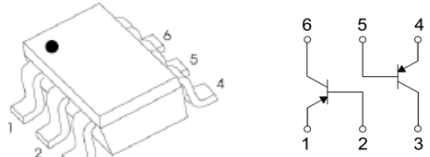


DUAL TRANSISTOR (PNP+PNP)	SOT-363 Plastic-Encapsulate Transistors
<p style="text-align: center;"><u>SOT-363</u></p>  <p style="text-align: center;">Marking :K4M</p>	<h3>Features</h3> <ul style="list-style-type: none"> • Epitaxial Planar Die Construction • Complementary NPN Type Available(MMDT 5551) • Ideal for Medium Power Amplification and Switching

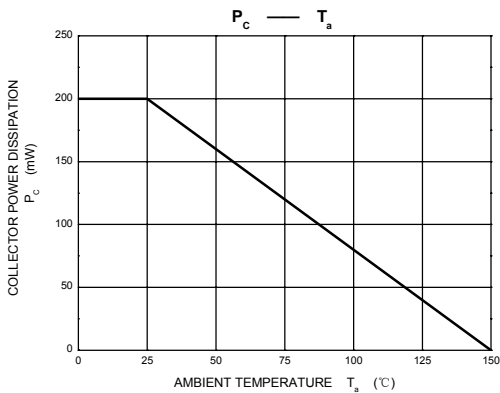
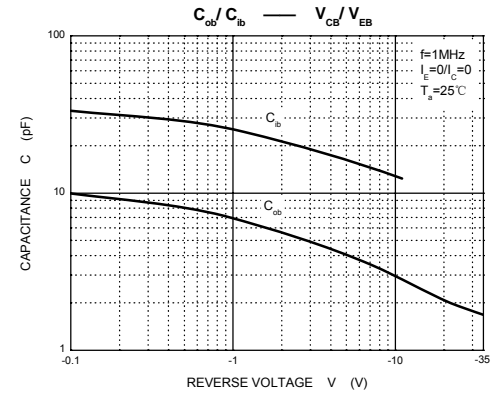
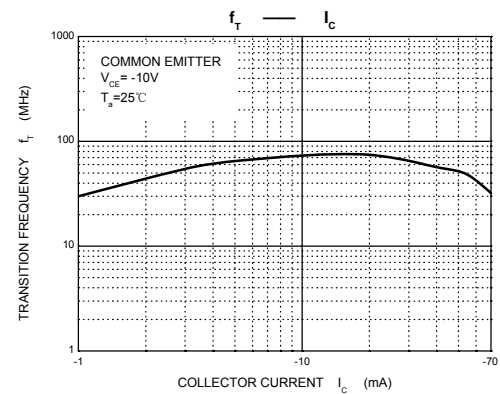
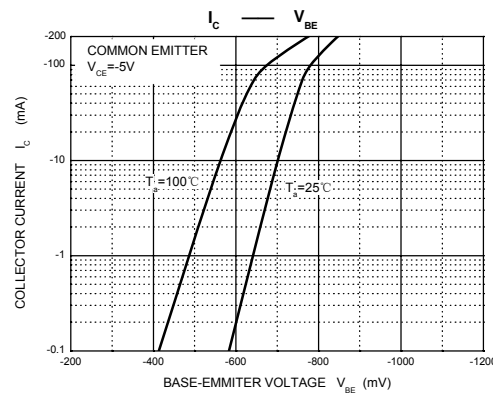
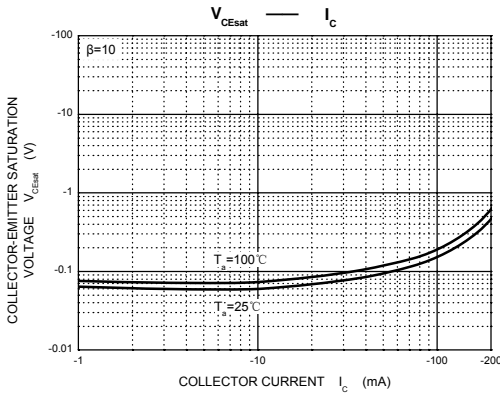
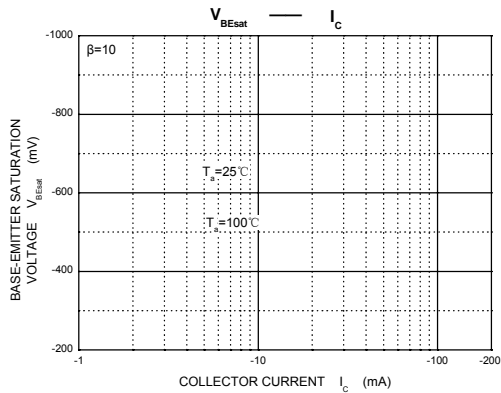
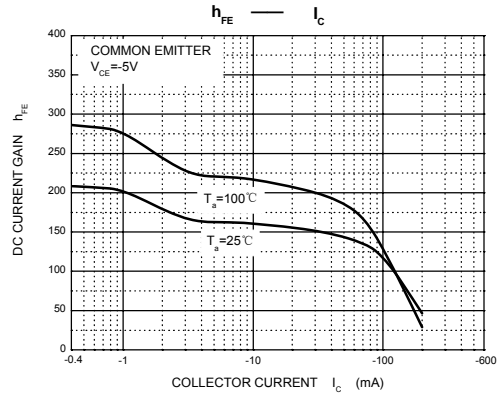
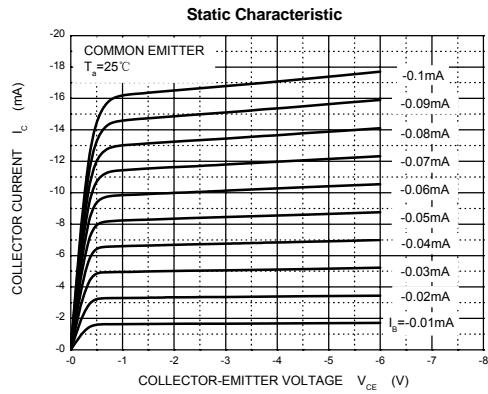
MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CBO}	Collector- Base Voltage	-160	V
V _{CEO}	Collector-Emitter Voltage	-150	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-0.2	A
P _C	Collector Power Dissipation	0.2	W
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C

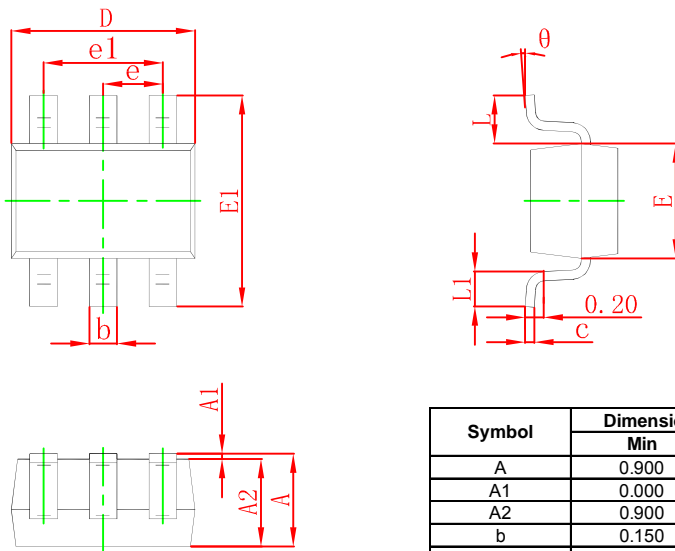
ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-160			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA, I _B =0	-150			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-120 V, I _E =0			-0.05	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-3V, I _C =0			-0.05	μA
DC current gain	h _{FE(1)}	V _{CE} =-5 V, I _C = -1mA	50			
	h _{FE(2)}	V _{CE} =-5 V, I _C = -10mA	100		300	
	h _{FE(3)}	V _{CE} =-5 V, I _C = -50mA	50			
Collector-emitter saturation voltage	V _{CE(sat)1}	I _C =-10 mA, I _B =-1mA			-0.2	V
	V _{CE(sat)2}	I _C =-50 mA, I _B =-5mA			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)1}	I _C = -10 mA, I _B =-1mA			-1	V
	V _{BE(sat)2}	I _C = -50 mA, I _B =-5mA			-1	V
Transition frequency	f _T	V _{CE} = -10V, I _C = -10mA, f = 100MHz	100			MHz
Output Capacitance	C _{ob}	V _{CB} =-10V, I _E = 0, f=1MHz			6	pF
Noise Figure	NF	V _{CE} = -5.0V, I _C = -200μA, R _S = 10Ω, f = 1.0kHz			8.0	dB

Typical Characteristics

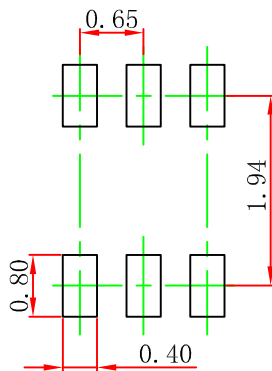


SOT-363 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.400	0.085	0.094
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
theta	0°	8°	0°	8°

SOT-363 Suggested Pad Layout



Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: ± 0.05mm.
 3. The pad layout is for reference purposes only.

单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)